

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
P-3454-USAPPLICATION NO.  
10/023,469INFORMATION DISCLOSURE  
STATEMENT BY APPLICANTAPPLICANT  
Boaz EitanCONFIRMATION NO.  
3554FILING DATE  
12/20/01GROUP  
2818

## U.S. PATENT DOCUMENTS

EXAM. INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W	3,895,360	07/15/1975	Cricchi et al.			
W	4,016,588	04/05/1977	Ohya et al.			
	4,017,888	04/12/1977	Christie et al.			
	4,151,021	04/24/1979	McElroy			
	4,173,766	11/06/1979	Hayes			
	4,173,791	11/06/1979	Bell			
	4,281,397	07/28/1981	Neal et al.			
	4,306,353	12/22/1981	Jacobs et al.			
	4,342,149	08/3/1982	Jacobs et al.			
	4,360,900	11/23/1982	Bate			
	4,380,057	04/12/1983	Kotecha et al.			
	4,388,705	06/14/1983	Sheppard			
	4,389,705	06/21/1983	Sheppard			
	4,471,373	09/11/1984	Shimizu et al.			
	4,527,257	07/02/1985	Cricchi			
	4,586,163	04/29/1986	Koike			
	4,630,085	12/16/1986	Koyama			
	4,667,217	05/19/1987	Janning			
	4,742,491	05/03/1988	Liang et al.			
	4,780,424	10/25/1988	Holler et al.			
	4,847,808	07/11/1989	Kobatake			
	4,870,470	09/26/1989	Bass, Jr. et al.			
	4,916,671	04/10/1990	Ichiguchi			
	4,941,028	07/10/1990	Chen et al.			
	5,021,999	06/4/1991	Kohda et al.			
	5,075,245	12/24/1991	Woo et al.			
W	5,117,389	05/26/1992	Yiu			
W	5,168,334	12/1/1992	Mitchell et al.			
W	5,172,338	12/15/1992	Mehrotra et al.			
W	5,175,120	12/29/1992	Lee			

EXAMINER

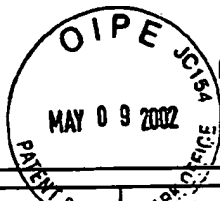
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W	5,214,303	05/25/1993	Aoki			
W	5,241,497	08/31/1993	Komarek			
	5,260,593	11/9/1993	Lee			
	5,268,861	12/07/1993	Hotta			
	5,289,412	02/22/1994	Frary et al.			
	5,293,563	03/8/1994	Ohta			
	5,305,262	04/19/1994	Yoneda			
	5,311,049	05/10/1994	Tsuruta			
	5,315,541	05/24/1994	Harari et al.			
	5,338,954	08/16/1994	Shimoji			
	5,345,425	09/6/1994	Shikatani			
	5,349,221	09/20/1994	Shimoji			
	5,350,710	09/27/1994	Hong et al.			
	5,359,554	10/25/1994	Odake et al.			
	5,375,094	12/20/1994	Naruke			
	5,393,701	02/28/1995	Ko et al.			
	5,394,355	2/28/1995	Uramoto et al.			
	5,399,891	03/21/1995	Yiu et al.			
	5,412,601	05/02/1995	Sawada et al.			
	5,414,693	05/09/1995	Ma et al.			
	5,418,176	5/23/1995	Yang et al.			
	5,418,743	5/23/1995	Tomioka et al.			
	5,422,844	06/06/1995	Wolstenholme et al.			
	5,424,978	06/13/1995	Wada et al.			
	5,426,605	06/20/1995	Van Berkel et al.			
	5,434,825	07/18/1995	Harari			
W	5,450,341	09/12/1995	Sawada et al.			
W	5,450,354	09/12/1995	Sawada et al.			
W	5,467,308	11/14/1995	Chang et al.			
W	5,477,499	12/19/1995	Van Buskirk et al.			

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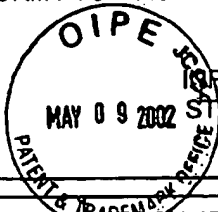
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W	5,495,440	02/27/1996	Asakura			
W	5,521,870	05/28/1996	Ishikawa			
	5,523,251	06/04/1996	Hong			
	5,553,018	09/03/1996	Wang et al.			
	5,583,808	12/10/1996	Brahmbhatt			
	5,599,727	02/04/1997	Hakozaki et al.			
	5,623,438	04/22/1997	Guritz et al.			
	5,654,568	08/05/1997	Nakao			
	5,656,513	08/12/1997	Wang et al.			
	5,661,060	08/26/1997	Gill et al.			
	5,683,925	11/04/1997	Irani et al.			
	5,712,814	01/27/1998	Fratin et al.			
	5,726,946	03/10/1998	Yamagata et al.			
	5,751,037	05/12/1998	Aozasa et al.			
	5,754,475	05/19/1998	Bill et al.			
	5,768,192	06/16/1998	Eitan			
	5,777,919	07/07/1998	Chi-Yung et al.			
	5,787,036	07/28/1998	Okazawa			
	5,793,079	08/11/1998	Georgescu et al.			
	5,825,686	10/20/1998	Schmitt-Landsiedel et al.			
	5,834,851	11/10/1998	Ikeda et al.			
	5,836,772	11/17/1998	Chang et al.			
	5,841,700	11/24/1998	Chang			
	5,847,441	12/8/1998	Cutter et al.			
	5,862,076	01/19/1999	Eitan			
W	5,864,164	01/26/1999	Wen			
W	5,870,335	02/09/1999	Khan et al.			
W	5,946,558	08/31/1999	Hsu			
W	5,949,728	09/07/1999	Liu et al.			
W	5,963,412	10/05/1999	En			

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
✓	5,963,465	10/05/1999	Eitan			
✓	5,973,373	10/26/1999	Krautschneider et al.			
	5,990,526	11/23/1999	Bez et al.			
	5,991,202	11/23/1999	Derhacobian et al.			
	6,011,725	01/04/2000	Eitan			
	6,018,186	01/25/2000	Hsu			
	6,020,241	02/01/2000	You et al.			
	6,028,324	02/22/2000	Su et al.			
	6,030,871	02/29/2000	Eitan			
	6,034,403	03/07/2000	Wu			
	6,063,666	05/16/2000	Chang et al.			
	6,081,456	06/27/2000	Dadashev			
	6,128,226	10/3/2000	Eitan et al.			
	6,134,156	10/17/2000	Eitan			
	6,137,718	10/24/2000	Reisinger			
	6,163,048	12/19/2000	Hirose et al.			
	6,201,282	03/13/2001	Eitan			
	08/902,890	07/30/1997	Eitan			
	08/905,286	07/30/1997	Eitan			
	09/211,981	12/14/1998	Eitan			
✓	09/348,720	07/06/1999	Eitan			
✓	09/413,408	10/06/1999	Eitan			
✓	09/536,125	03/28/2000	Eitan et al.			
✓	09/761,818	01/18/2001	Eliyahu et al.			

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## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
W	EP 0693781	01/24/1996					
W	EP 0751560	01/02/1997					
W	EP 1073120	01/31/2001					
	GB 2157489	10/23/1985					
	JP 09162314	06/20/1997					
	JP 404226071	08/14/1992					
	JP 04291962	10/16/1992					
	JP 05021758	01/29/1993					
	JP 07193151	07/28/1995					
W	WO 96/15553	05/23/1996					
W	WO 99/31670	06/24/1999					

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## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	
UN	Ricco, Bruno et al., "Nonvolatile Multilevel Memories for Digital Applications," <u>IEEE</u> , Vol. 86, No 12, pages 2399-2421, December, 1998.
UN	"2 Bit/Cell EEPROM Cell Using Band-To-Band Tunneling For Data Read-Out," <u>IBM Technical Disclosure Bulletin</u> , U.S. IBM Corp. NY Vol. 35, No. 4B, ISSN:0018-8689, pp. 136-140, September, 1992.
UN	Tseng, Hsing-Huang et al., "Thin CVD Stacked Gate Dielectric for ULSI Technology", <u>IEEE</u> , 0-7803-1450-6, pp. 321-324, 1993.
UN	Pickar, K.A., "Ion Implantation in Silicon," <u>Applied Solid State Science</u> , Vol. 5, R. Wolfe Edition, Academic Press, New York, pp. 151-249, 1975.
UN	Bhattacharyya et al., "FET Gate Structure for Nonvolatile N-Channel Read-Mostly Memory Device," <u>IBM Technical Disclosure Bulletin</u> , U.S. IBM Corp. Volume 18, No. 6, page 1768, November, 1975.
UN	Bude et al., "EEPROM/Flash Sub 3.0 V Drain-Source Bias Hot carrier Writing", <u>IEDM</u> 95, pp. 989-992.
UN	Bude et al., "Secondary Electron Flash - a High Performance, Low Power Flash Technology for 0.35 um and Below", <u>IEDM</u> 97, pp. 279-282.
UN	Bude et al., "Modeling Nonequilibrium Hot Carrier Device Effects", <u>Conference of Insulator Specialists of Europe</u> , Sweden, June, 1997.
UN	

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*V. Narayan*

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